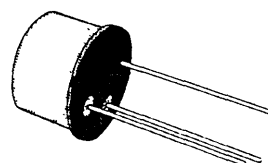


VHF OSCILLATOR POWER AMPLIFIER

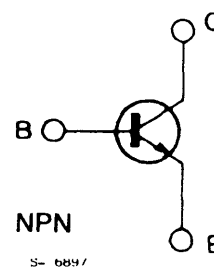
DESCRIPTION

The 2N4427 and BFR98 are silicon planar epitaxial NPN transistor in Jedec TO-39 metal case. They are designed for VHF class A, B, or C amplifier and oscillator applications.



TO-39

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|----------------|---|-------------|------------|
| V_{CBO} | Collector-base Voltage ($I_E = 0$) | 40 | V |
| V_{CEO} | Collector-emitter Voltage ($I_B = 0$) | 20 | V |
| V_{EBO} | Emitter-base Voltage ($I_C = 0$) | 3.5 | V |
| I_C | Collector Current | 0.5 | A |
| P_{tot} | Total Power Dissipation at $T_{case} \leq 25^\circ C$ | 3.5 | W |
| T_{stg}, T_J | Storage and Junction Temperature | - 65 to 200 | $^\circ C$ |

THERMAL DATA

| | | | | |
|-----------------|----------------------------------|-----|----|---------------|
| $R_{th J-case}$ | Thermal Resistance Junction-case | Max | 50 | $^{\circ}C/W$ |
|-----------------|----------------------------------|-----|----|---------------|

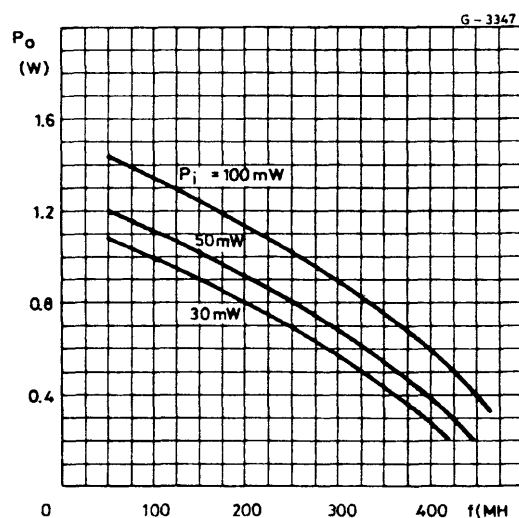
ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|------------------|---|--|---------|------|------|---------|
| I_{CEO} | Collector Cutoff Current ($I_B = 0$) | $V_{CE} = 12 V$ | | | 20 | μA |
| $V_{(BR)CBO}$ | Collector-base Breakdown Voltage ($I_E = 0$) | $I_C = 100 \mu A$ | 40 | | | V |
| $V_{CEO(sus)}^*$ | Collector-emitter Sustaining Voltage ($I_B = 0$) | $I_C = 5 mA$ | 20 | | | V |
| $V_{CE(sus)}^*$ | Collector-Emitter Sustaining Voltage ($R_{BE} = 10 \Omega$) | $I_C = 5 mA$ | 40 | | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage ($I_C = 0$) | $I_E = 100 \mu A$ | 3.5 | | | V |
| $V_{CE(sat)}^*$ | Collector-Emitter Saturation Voltage | $I_C = 100 mA$ $I_B = 20 mA$ | | | 0.5 | V |
| h_{FE}^* | DC Current Gain | $I_C = 100 mA$ $V_{CE} = 5 V$ $I_C = 360 mA$ $V_{CE} = 5 V$ | 10 5 | | 200 | |
| f_T | Transition Frequency | $I_C = 50 mA$ $V_{CE} = 15 V$ $f = 200 MHz$ | 500 | | | MHz |
| C_{CBO} | Collector-base Capacitance | $I_E = 0$ $V_{CB} = 12 V$ $f = 1 MHz$ | | | 4 | pF |
| P_o^{**} | Output Power | $V_{CC} = 12 V$ $P_i = 100 mW$ $f = 175 MHz$ | 1 | | | W |
| η^{**} | Collector Efficiency | $V_{CC} = 12 V$ $P_o = 1 W$ $f = 175 MHz$ | 50 | | | % |

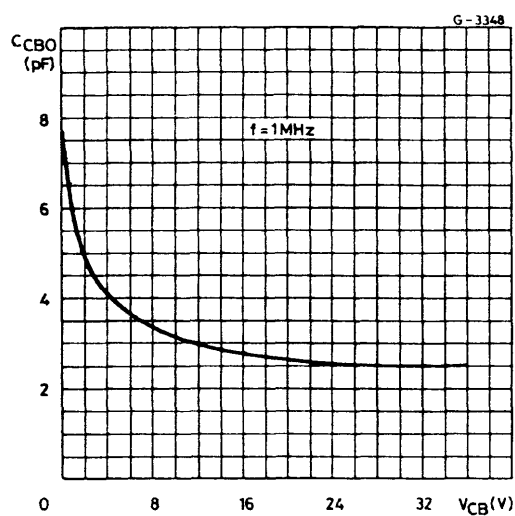
* Pulsed : pulse duration = 300 μs , duty cycle = 1 %.

** See test circuit.

RF Output Power.

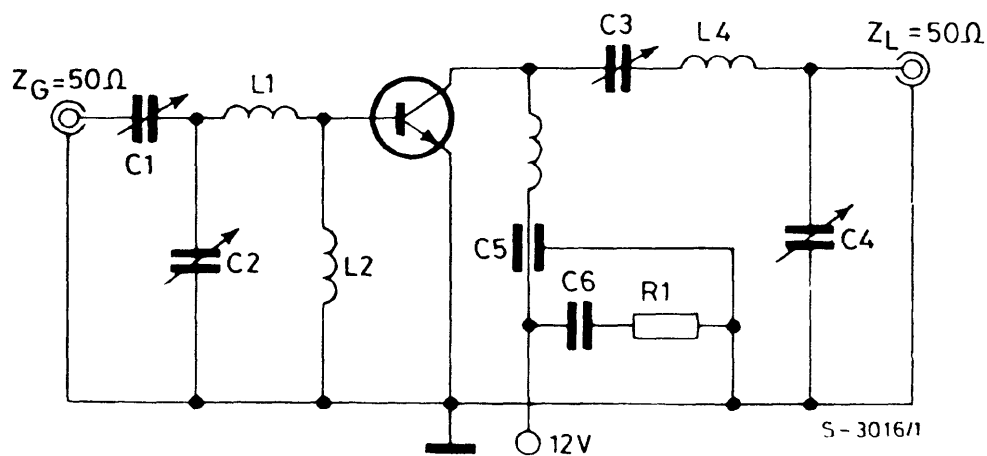


Collector-base Capacitance.



TEST CIRCUIT

Test Circuit for Power Output Measurement ($f = 175 \text{ MHz}$).



$C1, C2, C3, C4 = 3 \div 30 \text{ pF}$
 $C5 = 1000 \text{ pF}$
 $C6 = 20 \text{ k}\mu\text{F}$
 $R1 = 10 \text{ W}$

$L1 = 2 \text{ turns } 16 \text{ wire, } 3/16" \text{ ID, } 1/4" \text{ long}$
 $L2 = \text{ferrite choke, } Z = 450 \text{ W}$
 $L3 = 2 \text{ turns } 16 \text{ wire, } 1/4" \text{ ID, } 1/4" \text{ long}$
 $L4 = 4 \text{ turns } 16 \text{ wire, } 3/8" \text{ ID, } 3/8" \text{ long}$